

## 1. General description

WeEn Gen-2 Silicon Carbide MOSFET in a TO247-4L plastic package, designed for high frequency, high efficiency systems.



## 2. Features and benefits

- Kelvin source configuration
- Low specific on-resistance
- Optimized dynamic performance
- Robust gate design
- 0V turn-off  $V_{GS}$  for simple gate driving
- 100% UIS Tested
- Easy to parallel
- RoHS compliant

## 3. Applications

- PC/server/telecom power supplies
- UPS & Energy storage system
- Battery formation instrument
- PV MPPT and inverters
- EV Chargers
- Motor Drives

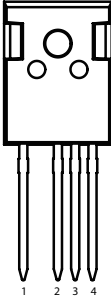
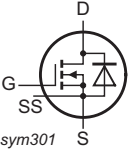
## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Notes	Values			Unit
Absolute maximum rating							
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		650			V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 18 V; T <sub>mb</sub> = 25 °C		218			A
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C, T <sub>j</sub> = 175 °C		625			W
T <sub>j</sub>	junction temperature			-55 to 175			°C
Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
Static characteristics							
R <sub>DS(on)</sub>	drain-source on-state resistance	V <sub>GS</sub> = 15 V; I <sub>D</sub> = 90 A; T <sub>j</sub> = 25 °C		-	12	-	mΩ
		V <sub>GS</sub> = 18 V; I <sub>D</sub> = 90 A; T <sub>j</sub> = 25 °C		-	9.5	12	mΩ
Dynamic characteristics							
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 90 A; V <sub>DS</sub> = 400 V; V <sub>GS</sub> = -4 V/18 V; T <sub>j</sub> = 25 °C		-	256	-	nC
Q <sub>GD</sub>	gate-drain charge			-	28	-	nC
Source-drain diode							
Q <sub>r</sub>	recovered charge	I <sub>SD</sub> = 90 A; di/dt = 500 A/μs; V <sub>DS</sub> = 400 V; T <sub>j</sub> = 25 °C		-	306	-	nC

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain		
2	S	source		
3	SS	source sense		
4	G	gate		
mb	D	mounting base; connected to drain		

6. Ordering information

Table 3. Ordering information

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
WNSC2M12065R	TO247-4L	WNSC2M12065R6Q	Tube	30	TO247N-4L	17-Dec-2021

7. Marking

Table 4. Marking codes

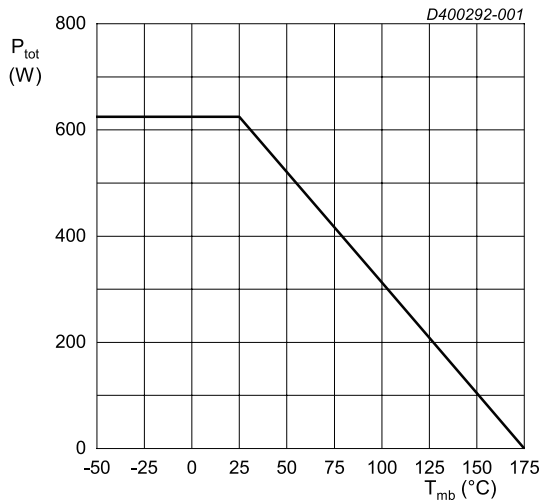
Type number	Marking codes
WNSC2M12065R	WNSC2M 12065R

## 8. Limiting values

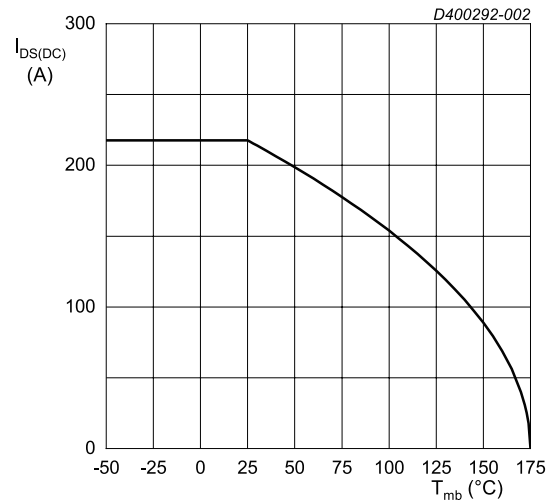
**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Notes	Values	Unit
$V_{DS}$	drain-source voltage	$25\text{ °C} \leq T_J \leq 175\text{ °C}$		650	V
$V_{GS,max}$	gate-source voltage	Absolute maximum values		-10 to 22	V
$V_{GS,op}$	gate-source voltage	Recommended operational values		-4 to 18	V
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C}$ ; $T_J = 175\text{ °C}$		625	W
$I_D$	drain current	$V_{GS} = 18\text{ V}$ ; $T_{mb} = 25\text{ °C}$		218	A
		$V_{GS} = 18\text{ V}$ ; $T_{mb} = 100\text{ °C}$		154	A
$I_{DM}$	peak drain current	pulse width $t_p$ limited by $T_{Jmax}$	Fig.17	435	A
$I_S$	continuous diode current	$V_{GS} = -4\text{ V}$ ; $T_{mb} = 25\text{ °C}$		118	A
$I_{SM}$	pulse diode current	$V_{GS} = -4\text{ V}$ ; pulse width $t_p$ limited by $T_{Jmax}$		435	A
$E_{as}$	single pulse drain-to-source avalanche	$I_{AS} = 37.8\text{ A}$ ; $L = 1\text{ mH}$ ; $V_{DD} = 100\text{ V}$ ; $T_J = 25\text{ °C}$		714	mJ
$T_{stg}$	storage temperature			-55 to 175	°C
$T_J$	junction temperature			-55 to 175	°C
$T_{sld(M)}$	peak soldering temperature			260	°C



**Fig. 1. Total power dissipation as a function of mounting base temperature; maximum values**



**Fig. 2. Continuous Drain Current as a function of mounting base temperature**

9. Thermal & Mechanical characteristics

Table 6. Thermal & Mechanical characteristics

Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base			-	0.24	-	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air		-	40	-	K/W
$M_d$	Mounting torque	M3 or 6 - 32 screw		-	-	0.6	Nm

Note: It is recommended that a metal washer is inserted between screw head and mounting tab.  
Do not use self-tapping screws.  
Device is ESD sensitive. Handling precautions are recommended.

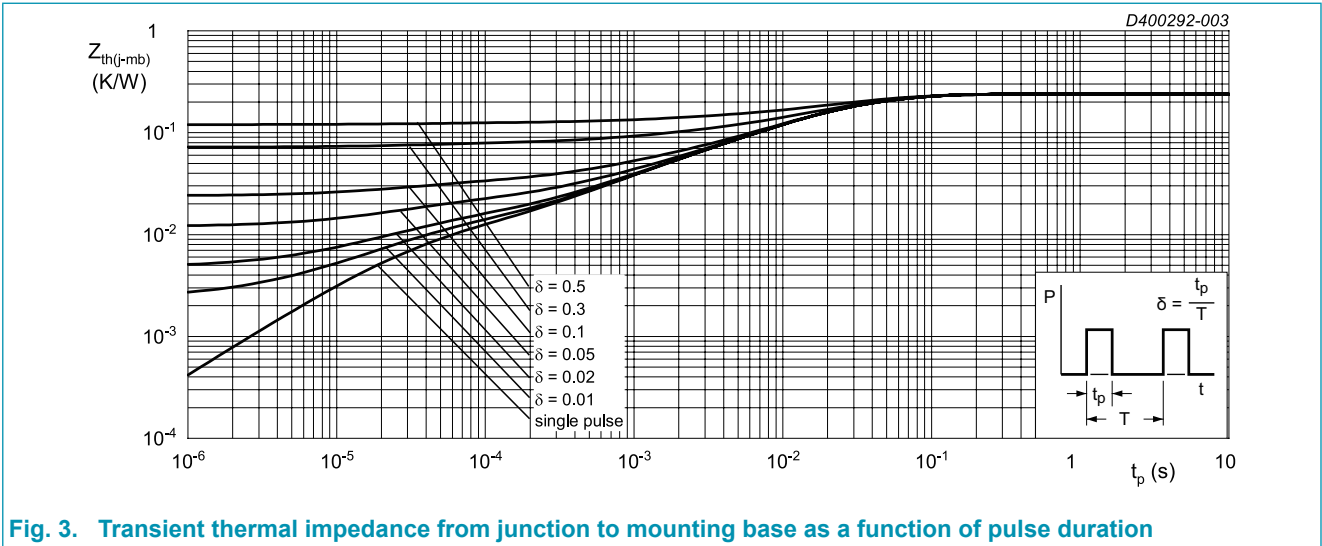
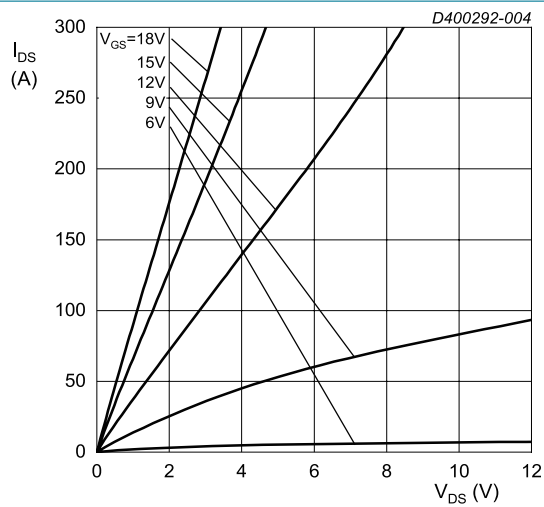


Fig. 3. Transient thermal impedance from junction to mounting base as a function of pulse duration

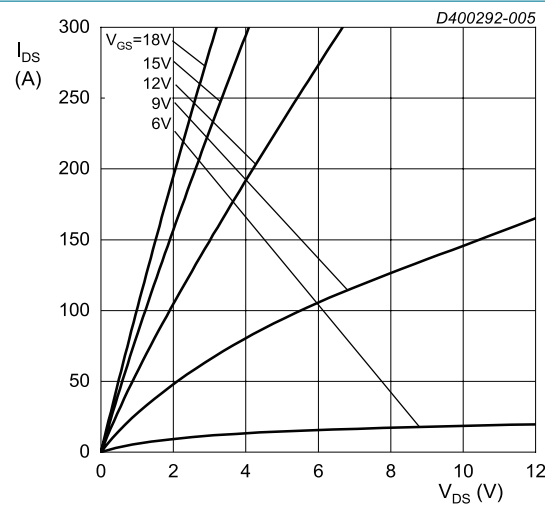
## 10. Characteristics

Table 7. Characteristics

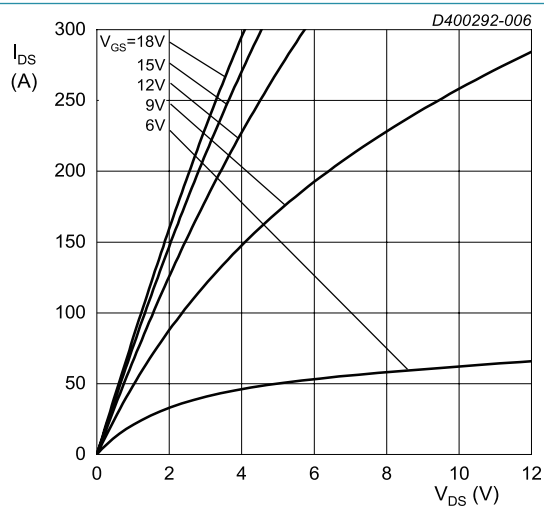
Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
Static characteristics							
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	I <sub>D</sub> = 100 μA; V <sub>GS</sub> = 0 V; T <sub>J</sub> = 25 °C		650	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	I <sub>D</sub> = 22.5 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>J</sub> = 25 °C		1.9	2.6	3.5	V
		I <sub>D</sub> = 22.5 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>J</sub> = 175 °C		-	1.9	-	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 650 V; V <sub>GS</sub> = 0 V; T <sub>J</sub> = 25 °C		-	0.1	50	μA
		V <sub>DS</sub> = 650 V; V <sub>GS</sub> = 0 V; T <sub>J</sub> = 175 °C		-	5	-	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 22 V; V <sub>DS</sub> = 0 V; T <sub>J</sub> = 25 °C		-	5	100	nA
		V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 0 V; T <sub>J</sub> = 25 °C		-	5	100	nA
R <sub>DS(on)</sub>	drain-source on-state resistance	V <sub>GS</sub> = 15 V; I <sub>D</sub> = 90 A; T <sub>J</sub> = 25 °C		-	12	-	mΩ
		V <sub>GS</sub> = 18 V; I <sub>D</sub> = 90 A; T <sub>J</sub> = 25 °C		-	9.5	12	mΩ
		V <sub>GS</sub> = 18 V; I <sub>D</sub> = 90 A; T <sub>J</sub> = 175 °C		-	11	-	mΩ
R <sub>G</sub>	gate resistance	f = 1 MHz; T <sub>J</sub> = 25 °C		-	0.96	-	Ω
g <sub>fs</sub>	transconductance	V <sub>DS</sub> = 20 V; I <sub>D</sub> = 90 A; T <sub>J</sub> = 25 °C		-	70	-	S
Dynamic characteristics							
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 90 A; V <sub>DS</sub> = 400 V; V <sub>GS</sub> = -4 V/18 V; T <sub>J</sub> = 25 °C		-	256	-	nC
Q <sub>GS</sub>	gate-source charge			-	100	-	nC
Q <sub>GD</sub>	gate-drain charge			-	28	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 400 V; V <sub>GS</sub> = 0 V; f = 1 MHz; T <sub>J</sub> = 25 °C		-	6150	-	pF
C <sub>oss</sub>	output capacitance			-	492	-	pF
C <sub>rss</sub>	reverse transfer capacitance			-	23.5	-	pF
E <sub>oss</sub>	Coss stored energy			-	39.4	-	μJ
t <sub>d(on)</sub>	turn-on delay time	V <sub>DS</sub> = 400 V; V <sub>GS</sub> = -4 V/18 V; R <sub>G(ext)</sub> = 5.1 Ω; I <sub>D</sub> = 45 A; L = 100 μH; T <sub>J</sub> = 25 °C		-	32	-	ns
t <sub>r</sub>	rise time			-	28	-	ns
t <sub>d(off)</sub>	turn-off delay time			-	77	-	ns
t <sub>f</sub>	fall time			-	17	-	ns
E <sub>on</sub>	turn-on energy <small>(SiC Diode FWD)</small>		Fig.19	-	170	-	μJ
E <sub>off</sub>	turn-off energy <small>(SiC Diode FWD)</small>		Fig.19	-	165	-	μJ
E <sub>on</sub>	turn-on energy <small>(Body Diode FWD)</small>		Fig.19	-	231	-	μJ
E <sub>off</sub>	turn-off energy <small>(Body Diode FWD)</small>		Fig.19	-	154	-	μJ
Source-drain diode							
V <sub>SD</sub>	source-drain voltage	V <sub>GS</sub> = 0 V; I <sub>SD</sub> = 90 A; T <sub>J</sub> = 25 °C		-	3.7	-	V
		V <sub>GS</sub> = -4 V; I <sub>SD</sub> = 90 A; T <sub>J</sub> = 25 °C		-	4.2	-	V
		V <sub>GS</sub> = -4 V; I <sub>SD</sub> = 90 A; T <sub>J</sub> = 175 °C		-	3.7	-	V
t <sub>rr</sub>	reverse recovery time	I <sub>SD</sub> = 90 A; di/dt = 500 A/μs; V <sub>DS</sub> = 400 V; T <sub>J</sub> = 25 °C		-	55	-	ns
Q <sub>r</sub>	recovered charge			-	306	-	nC
I <sub>rrm</sub>	reverse recovery current			-	11.1	-	A



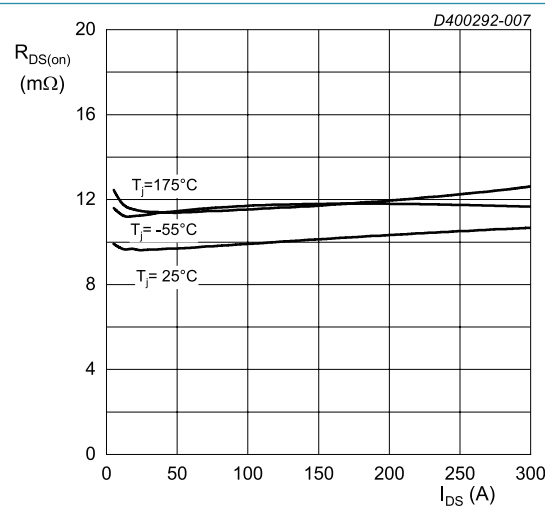
**Fig. 4.** Output characteristics; drain current as a function of drain-source voltage; typical values



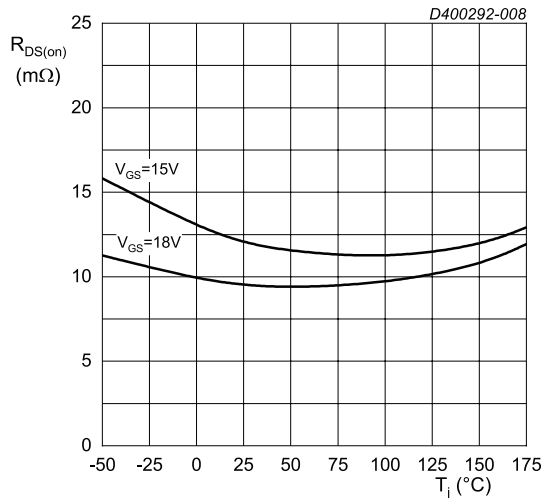
**Fig. 5.** Output characteristics; drain current as a function of drain-source voltage; typical values



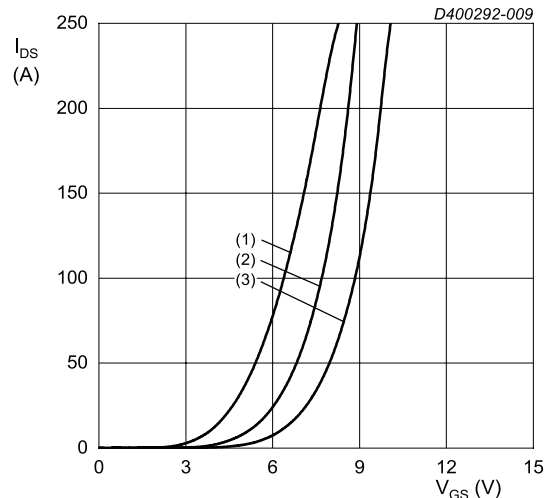
**Fig. 6.** Output characteristics; drain current as a function of drain-source voltage; typical values



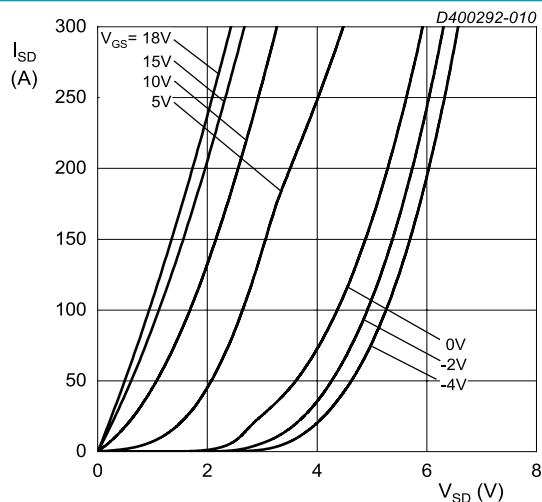
**Fig. 7.** Drain-source on-state resistance as a function of drain current; typical values



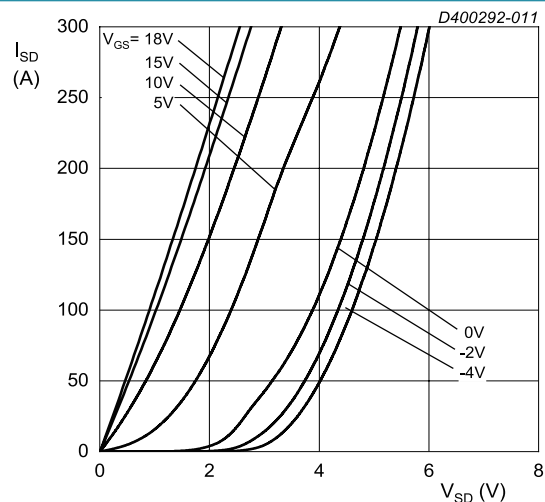
$I_{DS} = 90\text{ A}; t_p < 200\text{ }\mu\text{s}$   
**Fig. 8. Drain-source on-state resistance as a function of junction temperature**



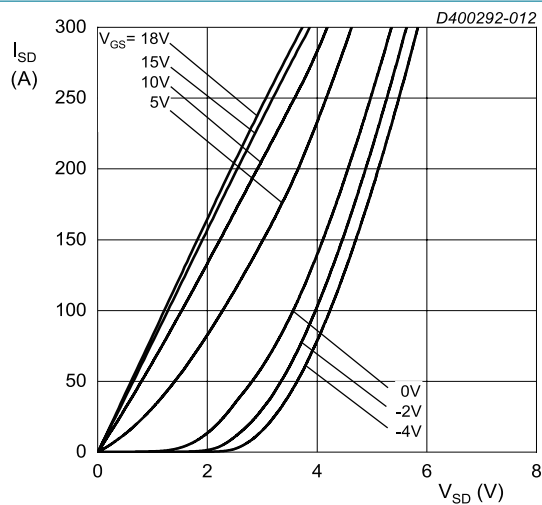
$V_{DS} = 20\text{ V}; t_p < 200\text{ }\mu\text{s}$   
(1)  $T_j = 175\text{ }^\circ\text{C}$   
(2)  $T_j = 25\text{ }^\circ\text{C}$   
(3)  $T_j = -55\text{ }^\circ\text{C}$   
**Fig. 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values**



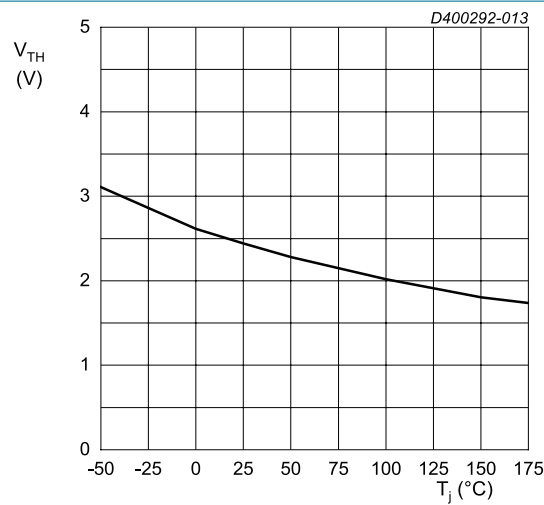
$T_j = -55\text{ }^\circ\text{C}; t_p < 200\text{ }\mu\text{s}$   
**Fig. 10. Body diode forward characteristics; typical values**



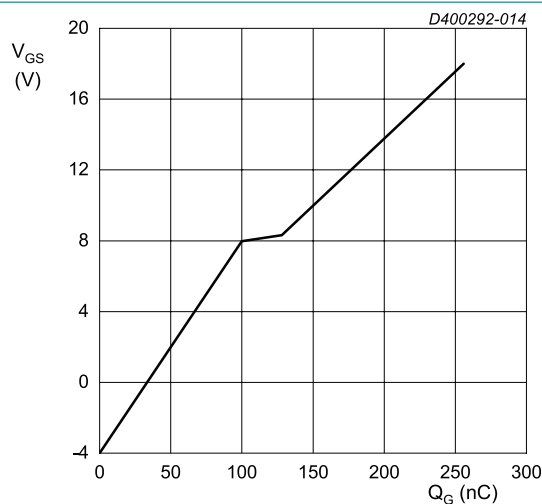
$T_j = 25\text{ }^\circ\text{C}; t_p < 200\text{ }\mu\text{s}$   
**Fig. 11. Body diode forward characteristics; typical values**



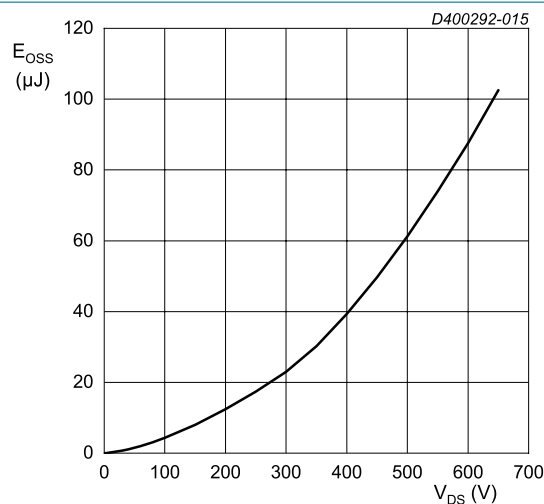
$T_j = 175\text{ }^{\circ}\text{C}$ ;  $t_p < 200\text{ }\mu\text{s}$   
**Fig. 12. Body diode forward characteristics; typical values**



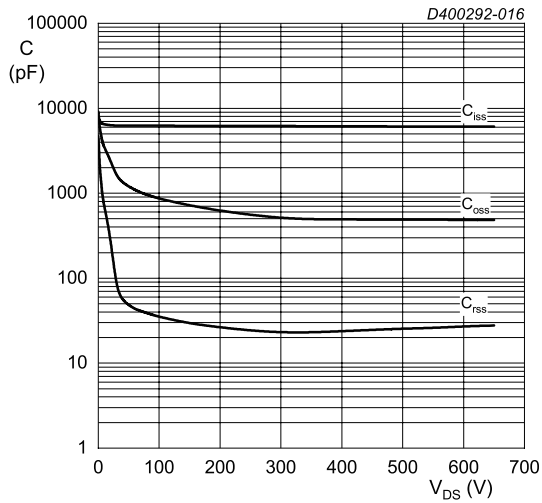
$V_{DS} = V_{GS}$ ;  $I_{DS} = 22.5\text{ mA}$   
**Fig. 13. Threshold voltage as a function of junction temperature**



$I_{DS} = 90\text{ A}$ ;  $I_{GS} = 0.1\text{ mA}$ ;  $V_{DS} = 400\text{ V}$ ;  $T_j = 25\text{ }^{\circ}\text{C}$   
**Fig. 14. Gate-source voltage as a function of gate charge; typical values**

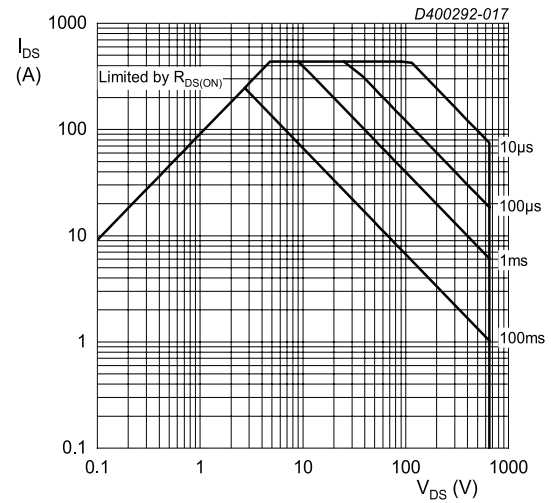


**Fig. 15. Output capacitor stored energy as a function of drain-source voltage**



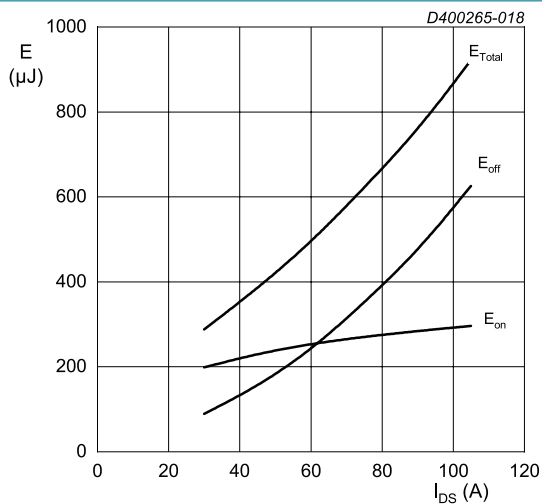
$V_{DS} = 0 - 650 \text{ V}$   
 $T_j = 25^\circ\text{C}$ ;  $V_{AC} = 25 \text{ mV}$ ;  $f = 1 \text{ MHz}$

**Fig. 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values**



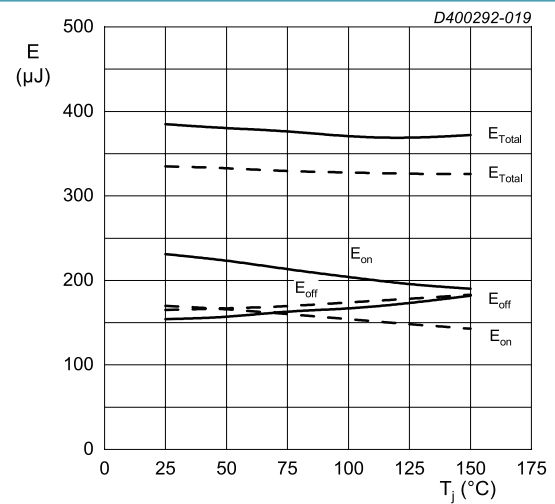
$T_j = 25^\circ\text{C}$ ;  $D = 0$   
 Parameter:  $t_p$

**Fig. 17. Forward bias safe operating area**



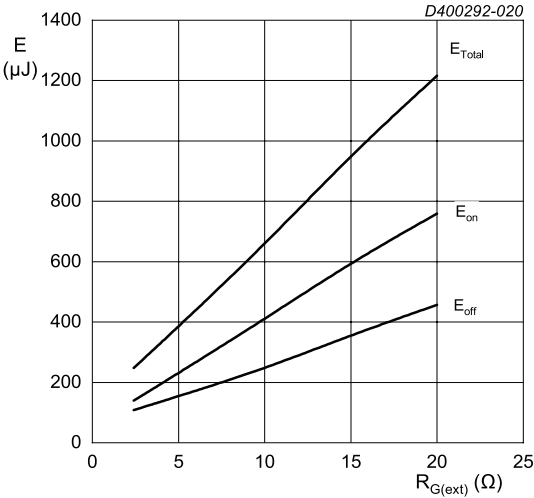
$T_j = 25^\circ\text{C}$ ;  $V_{DD} = 400 \text{ V}$ ;  $R_{G(ext)} = 5.1 \Omega$ ;  
 $V_{GS} = -4 \text{ V}/18 \text{ V}$ ;  $L = 100 \mu\text{H}$   
 FWD = WNSC2M12065R

**Fig. 18. Clamped Inductive Switching Energy as a function of drain current**



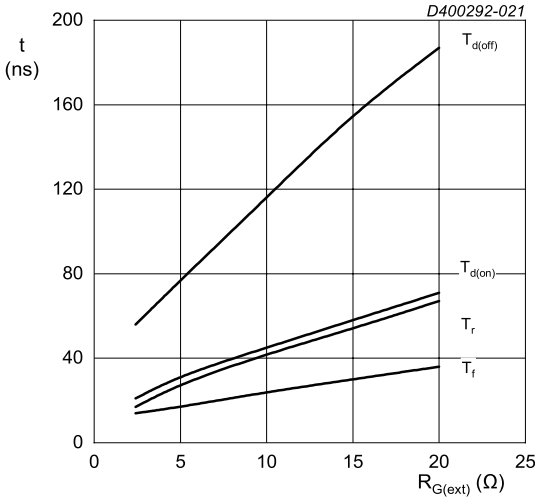
$I_{DS} = 45 \text{ A}$ ;  $V_{DD} = 400 \text{ V}$ ;  $R_{G(ext)} = 5.1 \Omega$ ;  
 $V_{GS} = -4 \text{ V}/18 \text{ V}$ ;  $L = 100 \mu\text{H}$   
 FWD = WNSC2M12065R  
 FWD = WNSC6D30650W(---)

**Fig. 19. Clamped Inductive Switching Energy as a function of junction temperature**



$T_j = 25\text{ }^{\circ}\text{C}$ ;  $V_{DD} = 400\text{ V}$ ;  $I_{DS} = 45\text{ A}$ ;  $V_{GS} = -4\text{ V}/18\text{ V}$   
FWD = WNSC2M12065R;  $L = 100\text{ }\mu\text{H}$

Fig. 20. Clamped Inductive Switching Energy as a function of external gate resistance



$T_j = 25\text{ }^{\circ}\text{C}$ ;  $V_{DD} = 400\text{ V}$ ;  $I_{DS} = 45\text{ A}$ ;  $V_{GS} = -4\text{ V}/18\text{ V}$   
FWD = WNSC2M12065R;  $L = 100\text{ }\mu\text{H}$

Fig. 21. Switching time as a function of external gate resistance

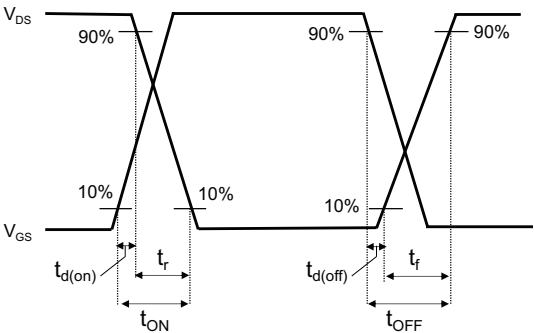
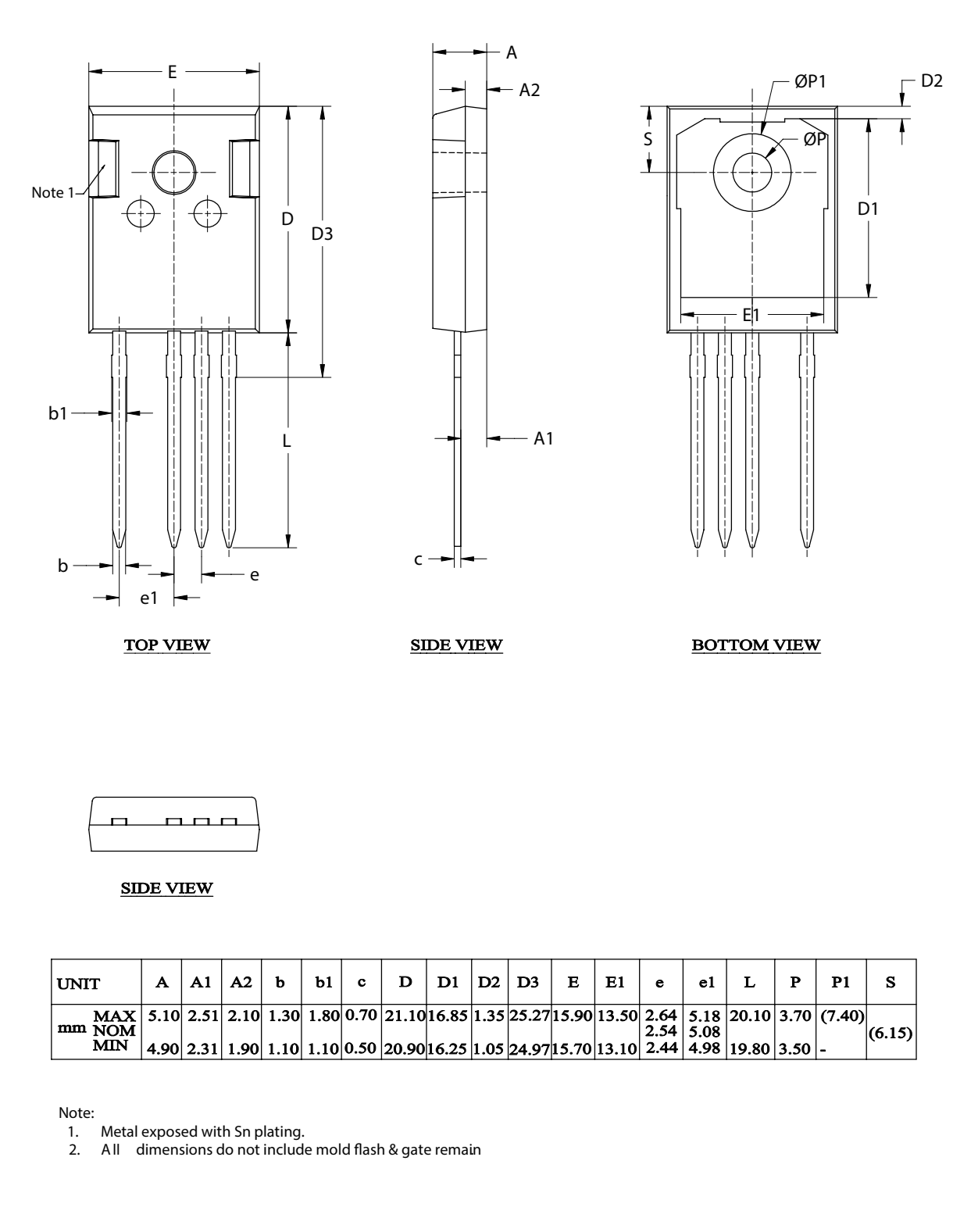


Fig. 22. Switching time definition

11. Package outline

Plastic single-ended through-hole package; heatsink mounted;1 mounting hole; 4 leads TO-247

TO247-4L



## 12. Legal information

### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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